

REMARKS

Claims 1-11 are pending in the application. Claims 1, 9, 10, and 11 have been amended, leaving claims 1-11 for consideration upon entry of the present Amendment. Support for the amendment can be found at page 5, line 28 to page 6, line 2 and in the claims as originally filed. In addition, the Examiner had suggested a new title. Applicant has revised the title.

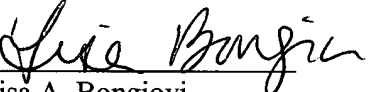
In addition, attached hereto is a marked-up version of the changes made to the application. The attached page is captioned "**Version with Markings to Show Changes Made.**"

It is respectfully submitted that the instant application is in condition for allowance. Accordingly, it is respectfully requested that this application be allowed and a Notice of Allowance issued. If the Examiner believes that a telephone conference with Applicant's attorneys would be advantageous to the disposition of this case, the Examiner is cordially requested to telephone the undersigned.

In the event the Commissioner of Patents and Trademarks deems additional fees to be due in connection with this application, Applicant's attorney hereby authorizes that such fee be charged to Deposit Account No. 06-1130.

Respectfully submitted,

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Version with Markings to Show Changes Made

IN THE TITLE:

Please amend the title in "marked up" format, as follows:

ELECTROLUMINESCENCE DISPLAY DEVICE WITH A DOUBLE GATE TYPE THIN FILM TRANSISTOR HAVING A LIGHTLY DOPED DRAIN STRUCTURE

IN THE CLAIMS:

Please amend claims 1, 9, 10, and 11 in "marked up" format, as follows:

1. (Marked up/Twice Amended) An electroluminescence device, comprising:
 - an electroluminescence element having a light emissive layer provided between first and second electrodes;
 - a first thin film transistor receiving a selection signal at its gate to acquire a data signal; and
 - a second thin film transistor provided between a driving power supply and said electroluminescence element, and controlling power supplied from said driving power supply to said electroluminescence element in accordance with the data signal supplied from said first thin film transistor; wherein
 - said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has at least one of an n-channel, an offset structure, and a multigate structure; and
 - said second thin film transistor has a p-channel.
9. (Marked up/Twice Amended) An electroluminescence display device, comprising:
 - an electroluminescence element having a light emissive layer provided between an anode and a cathode;
 - a first thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a source connected to a storage capacitor, a drain connected to a drain signal line, and a gate electrode provided over a channel of said active layer and connected to a gate signal line; and
 - a second thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a drain connected to a driving power supply of said electroluminescence element, and a gate electrode connected to the source of said first thin film transistor; wherein
 - said first thin film transistor is a double gate type having a lightly doped drain

structure, said first thin film transistor has at least one of an n-channel, an offset structure, and a multigate structure; and

said second thin film transistor has a p-channel.

10. (Marked up/ Twice Amended) An electroluminescence display device, comprising:
an electroluminescence element having a light emissive layer provided between an anode and a cathode;

a first thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a source connected to a storage capacitor, a drain connected to a drain signal line, and a gate electrode provided under a channel of said active layer and connected to a gate signal line; and

a second thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a drain connected to a driving power supply of said electroluminescence element, and a gate electrode connected to the source of said first thin film transistor; wherein

said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has at least one of an n-channel, an offset structure, and a multigate structure; and

said second thin film transistor has a p-channel.

11. (Marked up/ Twice Amended) A light emissive device, comprising:
a light emissive element having a light emissive layer provided between first and second electrodes;

a first thin film transistor receiving a selection signal at its gate to acquire a data signal; and

a second thin film transistor provided between a driving power supply and said element, and controlling power supplied from said driving power supply to said element in accordance with the data signal supplied from said first thin film transistor; wherein

said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has at least one of an n-channel, an offset structure, and a multigate structure; and

said second thin film transistor has a p-channel.